

Page 6, line 6, please add --FIGURES 5A-5E show cross-sectional views of a
structure fabricated in accordance with another method of the present invention.--

In the Claims:

Please cancel claims 1-39 and 52-67.

Please add claims 68-73.

--68. The semiconductor device of claim 40, wherein said first insulator layer is
at least 2 microns thicker than said at least one metal contact.

69. The semiconductor device of claim 40, wherein said metal pad comprises a
metal stack comprising four different metal levels.

70. The semiconductor device of claim 69, wherein said metal levels comprise
Zirconium, Nickel, Copper and Gold.

71. A semiconductor device formed on a semiconductor substrate having at
least one metal contact formed thereon, said semiconductor device comprising:

a first insulator layer overlying said at least one metal contact;

at least one metal pad overlying said first insulator layer and being in contact
with the at least one metal contact;

a second insulator layer overlying said at least one metal pad; and

at least one solder contact formed in said second insulator layer and being in contact with said at least one metal pad, said solder contact having a diameter between 2 and 100 microns.

72. The semiconductor device of claim 71, wherein said at least one solder contact has a diameter of approximately 2 microns.

73. A semiconductor device formed on a semiconductor substrate having at least one metal contact formed thereon, said semiconductor device comprising:

a first insulator layer overlying said at least one metal contact;

at least one metal pad overlying said first insulator layer and being in contact with the at least one metal contact;

a second insulator layer overlying said at least one metal pad; and

at least one solder contact formed in said second insulator layer and being in contact with said at least one metal pad, wherein said solder contact is formed by depositing a photoresist layer over said second insulating layer, forming at least one hole in said second insulating layer and the photoresist layer to expose said at least one metal pad, applying a solder layer over the photoresist layer and in the at least one hole to form at least one solder area in the hole which is in contact with said at least one metal pad, and simultaneously removing the photoresist layer and solder layer using a tape liftoff process while leaving said at least one solder contact in contact with said at least one metal pad.--